

WHAT IS CLAIMED IS:

1. A semiconductor device comprising semiconductor elements obtained by cutting a semiconductor wafer having an integrated circuit and an electrode pad formed on one side along a cutting scribe line, a stress cushioning layer installed on said semiconductor elements, a lead wire portion extending from said electrode pad to a top of said stress cushioning layer through an opening formed in said stress cushioning layer on said electrode pad, external electrodes arranged on said lead wire portion on said top of said stress cushioning layer, and a conductor protective layer installed on said stress cushioning layer excluding said external electrode arranged portion and on a conductor portion, wherein said stress cushioning layer, said lead wire portion, said conductor protective layer, (and said external electrodes have means for forming each end face on an end surface of said semiconductor elements inside said cutting scribe line and exposing a range from said end face on said end surface of said semiconductor elements to an inside of said scribe line.)
2. A semiconductor device according to Claim 1, wherein said end face of said conductor protective

player is formed inside said end face of said stress cushioning layer.

3. A semiconductor device according to Claim 1,  
5 wherein said end face of said conductor protective player is formed outside said end face of said stress cushioning layer.

4. A semiconductor device according to any of Claims 1  
10 to 3, wherein an end area of said stress cushioning layer is formed so as to become taperingly thinner toward the said end face.

5. A semiconductor device comprising semiconductor  
15 elements obtained by cutting a semiconductor wafer having an integrated circuit and an electrode pad formed on one side along a cutting scribe line, a semiconductor element protective layer installed on said semiconductor elements, a stress cushioning layer  
20 installed on said semiconductor element protective layer, a first opening formed in said semiconductor element protective layer on said electrode pad, a second opening formed in said stress cushioning layer on said electrode pad, a lead wire portion extending  
25 to a top of said stress cushioning layer through said

first opening and said second opening respectively  
from said electrode pad, external electrodes arranged  
on said lead wire portion on said top of said stress  
cushioning layer, and a conductor protective layer  
5 installed on said stress cushioning layer excluding  
said external electrode arranged portion and on said  
conductor portion, wherein said semiconductor element  
protective layer, said stress cushioning layer, said  
lead wire portion, said conductor protective layer,  
10 and said external electrodes have means for forming  
each end face on an end surface of said semiconductor  
elements inside a cutting scribe line and exposing a  
range from said end face on said end surface of said  
semiconductor elements to an inside of said scribe  
15 line.

6. A semiconductor device according to Claim 5,  
wherein said end face of said conductor protective  
<sup>112</sup>player is formed inside said end face of said stress  
20 cushioning layer.

7. A semiconductor device according to Claim 5,  
wherein said end face of said conductor protective  
player is formed outside said end face of said stress  
25 cushioning layer.

8. A semiconductor device according to claim 6 or 7,  
wherein said end face of said semiconductor element  
protective player is formed outside said end face of  
said stress cushioning layer.

9. A semiconductor device according to Claim 6 or 7,  
wherein said end face of said semiconductor element  
protective player is formed inside said end face of  
said stress cushioning layer.

10. A semiconductor device according to any of Claims  
4 to 9, wherein an end area of said stress cushioning  
layer is formed so as to become taperingly thinner  
toward the said end face.

11. A semiconductor device manufacturing method  
comprising a first step of forming a plurality of  
semiconductor elements having an integrated circuit  
and an electrode pad on a circuit forming surface of a  
semiconductor wafer, a second step of forming a stress  
cushioning layer on a plurality of semiconductor  
elements, a third step of forming an opening in an  
electrode pad of said stress cushioning layer and  
forming a notch wider than a width of a scribe line in

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said stress cushioning layer on said cutting scribe line of said semiconductor wafer, a fourth step of forming a lead wire portion extending from said electrode pad to said stress cushioning layer via said opening, a fifth step of forming a conductor protective layer which covers said stress cushioning layer and said lead wire portion and has an external electrode connection window portion on said lead wire portion and a notch at a position corresponding to a notch of said stress cushioning layer, a sixth step of forming an external electrode in said external electrode connection window portion, and a seventh step of cutting said semiconductor wafer along said cutting scribe line and obtaining a plurality of semiconductor devices in minimum units.

12. A semiconductor device manufacturing method according to Claim 11, wherein an end face obtained by said notch of said conductor protective layer at said Step 5 is formed inside said semiconductor wafer cutting scribe line.

13. A semiconductor device manufacturing method according to Claim 12, wherein said end face obtained by said notch of said conductor protective layer at

said Step 5 is formed inside an end face formed by said notch of said stress cushioning layer.

14. A semiconductor device manufacturing method according to Claim 12, wherein said end face obtained by said notch of said conductor protective layer at said Step 5 is formed outside an end face formed by said notch of said stress cushioning layer.

15. A semiconductor device manufacturing method comprising a first step of forming a plurality of semiconductor elements having an integrated circuit and an electrode pad on a circuit forming surface of a semiconductor wafer, a second step of forming a semiconductor element protective layer on a plurality of semiconductor elements, a third step of forming a first opening in an electrode pad of said semiconductor element protective layer and forming a notch wider than a width of a scribe line in said semiconductor element protective layer on said cutting scribe line of said semiconductor wafer, a fourth step of forming a stress cushioning layer on said semiconductor element protective layer, a fifth step of forming a second opening in said electrode pad of said stress cushioning layer and forming a notch at a

position corresponding to a notch of said semiconductor element protective layer in said stress cushioning layer on said cutting scribe line of said semiconductor wafer, a sixth step of forming a lead wire portion extending from said electrode pad to said stress cushioning layer via said first opening and said second opening, a seventh step of forming a conductor protective layer which covers said stress cushioning layer and said lead wire portion and has an external electrode connection window portion on said lead wire portion and a notch at a position corresponding to said notch of said stress cushioning layer, an eighth step of forming an external electrode in said external electrode connection window portion, and a ninth step of cutting said semiconductor wafer along said cutting scribe line and obtaining a plurality of semiconductor devices in minimum units.

16. A semiconductor device manufacturing method according to Claim 15, wherein an end face obtained by said notch of said stress cushioning layer at said Step 4 is formed inside said semiconductor wafer cutting scribe line.

17. A semiconductor device manufacturing method

according to Claim 16, wherein said end face obtained by said notch of said stress cushioning layer at said Step 4 is formed inside an end face formed by said notch of said semiconductor element protective layer.

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18. A semiconductor device manufacturing method according to Claim 16, wherein said end face obtained by said notch of said stress cushioning layer at said Step 4 is formed outside an end face formed by said notch of said semiconductor element protective layer.

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19. A semiconductor device manufacturing method according to Claim 16, wherein said end face obtained by said notch of said stress cushioning layer at said Step 4 is formed so as to be installed on the same plane as that of an end face formed by said notch of said semiconductor element protective layer.

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20. A semiconductor device manufacturing method according to Claim 15, wherein an end face obtained by said notch of said conductor protective layer at said Step 7 is formed inside said semiconductor wafer cutting scribe line.

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21. A semiconductor device manufacturing method

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according to Claim 20, wherein said end face obtained  
by said notch of said conductor protective layer at  
said Step 7 is formed inside an end face formed by  
said notch of said semiconductor element protective  
5 layer.

22. A semiconductor device manufacturing method  
according to Claim 20, wherein said end face obtained  
by said notch of said conductor protective layer at  
10 said Step 7 is formed outside an end face formed by  
said notch of said semiconductor element protective  
layer.

23. A semiconductor device manufacturing method  
15 according to Claim 20, wherein said end face obtained  
by said notch of said conductor protective layer at  
said Step 7 is formed so as to be installed on the  
same plane as that of an end face formed by said notch  
of said semiconductor element protective layer.

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24. A semiconductor device manufacturing method  
according to Claim 16 or 20, wherein said end face  
obtained by said notch of said conductor protective  
layer at said Step 7 is formed inside an end face  
25 formed by said notch of said semiconductor element

protective layer and an end face formed by said notch  
of said stress cushioning layer.

25. A semiconductor device manufacturing method  
5 according to Claim 16 or 20, wherein said end face  
obtained by said notch of said conductor protective  
layer at said Step 7 is formed outside an end face  
formed by said notch of said semiconductor element  
protective layer and an end face formed by said notch  
10 of said stress cushioning layer.

26. A semiconductor device manufacturing method  
according to Claim 16 or 20, wherein said end face  
obtained by said notch of said conductor protective  
15 layer at said Step 7 is formed between an end face  
formed by said notch of said semiconductor element  
protective layer and an end face formed by said notch  
of said stress cushioning layer.

20 27. A semiconductor device manufacturing method  
according to Claim 16 or 20, wherein said end face  
obtained by said notch of said conductor protective  
layer at said Step 7 is formed to be installed on the  
same plane as that of an end face formed by said notch  
25 of said semiconductor element protective layer and an

country	year	age	sex	height	weight	fat	muscle	bone	skin	visceral	total
USA	1980	20-29	M	175	75	15	35	12	10	10	100
USA	1980	30-39	M	175	75	15	35	12	10	10	100
USA	1980	40-49	M	175	75	15	35	12	10	10	100
USA	1980	50-59	M	175	75	15	35	12	10	10	100
USA	1980	60-69	M	175	75	15	35	12	10	10	100
USA	1980	70-79	M	175	75	15	35	12	10	10	100
USA	1980	80-89	M	175	75	15	35	12	10	10	100
USA	1980	90-99	M	175	75	15	35	12	10	10	100
USA	1980	20-29	F	160	60	15	35	12	10	10	100
USA	1980	30-39	F	160	60	15	35	12	10	10	100
USA	1980	40-49	F	160	60	15	35	12	10	10	100
USA	1980	50-59	F	160	60	15	35	12	10	10	100
USA	1980	60-69	F	160	60	15	35	12	10	10	100
USA	1980	70-79	F	160	60	15	35	12	10	10	100
USA	1980	80-89	F	160	60	15	35	12	10	10	100
USA	1980	90-99	F	160	60	15	35	12	10	10	100
USA	1980	20-29	M	175	75	15	35	12	10	10	100
USA	1980	30-39	M	175	75	15	35	12	10	10	100
USA	1980	40-49	M	175	75	15	35	12	10	10	100
USA	1980	50-59	M	175	75	15	35	12	10	10	100
USA	1980	60-69	M	175	75	15	35	12	10	10	100
USA	1980	70-79	M	175	75	15	35	12	10	10	100
USA	1980	80-89	M	175	75	15	35	12	10	10	100
USA	1980	90-99	M	175	75	15	35	12	10	10	100
USA	1980	20-29	F	160	60	15	35	12	10	10	100
USA	1980	30-39	F	160	60	15	35	12	10	10	100
USA	1980	40-49	F	160	60	15	35	12	10	10	100
USA	1980	50-59	F	160	60	15	35	12	10	10	100
USA	1980	60-69	F	160	60	15	35	12	10	10	100
USA	1980	70-79	F	160	60	15	35	12	10	10	100
USA	1980	80-89	F	160	60	15	35	12	10	10	100
USA	1980	90-99	F	160	60	15	35	12	10	10	100
USA	1980	20-29	M	175	75	15	35	12	10	10	100
USA	1980	30-39	M	175	75	15	35	12	10	10	100
USA	1980	40-49	M	175	75	15	35	12	10	10	100
USA	1980	50-59	M	175	75	15	35	12	10	10	100
USA	1980	60-69	M	175	75	15	35	12	10	10	100
USA	1980	70-79									